

110 Watts - 50 Volts, 330µs, 10% Radar 1200 - 1400 MHz

GENERAL DESCRIPTION

The 1214-110M is an internally matched, COMMON BASE transistor capable of providing 110 Watts of pulsed RF output power at 330 μs pulse width, 10% duty factor across the band 1200 to 1400 MHz. This hermetically solder-sealed transistor is specifically designed for L-Band radar applications. It utilizes gold metallization and diffused emitter ballasting to provide high reliability and supreme ruggedness.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C 270 Watts

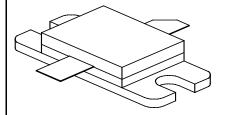
Maximum Voltage and Current

BVces Collector to Emitter Voltage 75 Volts
BVebo Emitter to Base Voltage 3.0 Volts
Ic Collector Current 8 Amps

Maximum Temperatures

Storage Temperature $-65 \text{ to} + 200^{\circ}\text{C}$ Operating Junction Temperature $+200^{\circ}\text{C}$

CASE OUTLINE 55KT, STYLE 1



ELECTRICAL CHARACTERISTICS @ 25 $^{\rm o}$ C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pg ηc Rl Droop Flatness VSWR¹ VSWRs	Power Out Power Gain Collector Efficiency Input Return loss Droop Flatness Load Mismatch Tolerance Load Mismatch - Stability	Freq = 1200 – 1400 MHz Vcc = 50 Volts Pin = 20 Watts Pulse Width = 330µs Duty Factor = 10%	110 7.4 50 10	55	0.5 1.25 3:1 1.5:1	Watts dB % dB dB

FUNCTIONAL CHARACTERISTICS @ 25°C

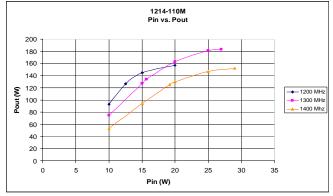
Bvces Ices θjc¹	Collector to Emitter Breakdown Collector to Emitter Leakage Thermal Resistance	Ic = 100 mA Vce = 50 Volts Rated Pulse Condition	75	10 0.65	Volts mA °C/W
Ojc	Thermal Resistance	rated I tilbe Condition		0.05	C/ VV

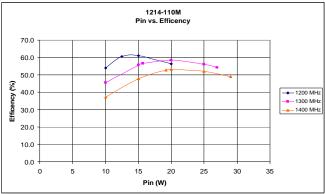
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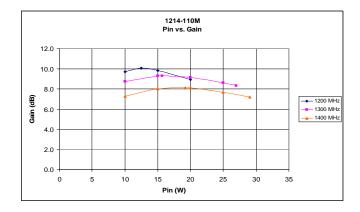
Microsemi Corp. 3000 Oakmead Village Drive, Santa Clara, CA 95051-0808 Tel. 408 / 986-8031 Fax 408 /869-2324



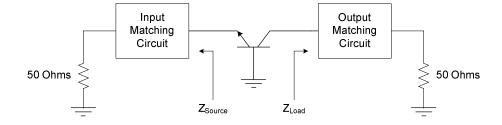
Performance Curves







Impedance Information



Frequencies (MHz)	$Z_{\scriptscriptstyle Source}(\Omega)$	$Z_{Load}(\Omega)^{2}$
1200	3.36-j3.12	4.97+j0.15
1300	3.5-j2.4	5.33-j2.86
1400	3.81-j1.3	2.88-j3.86

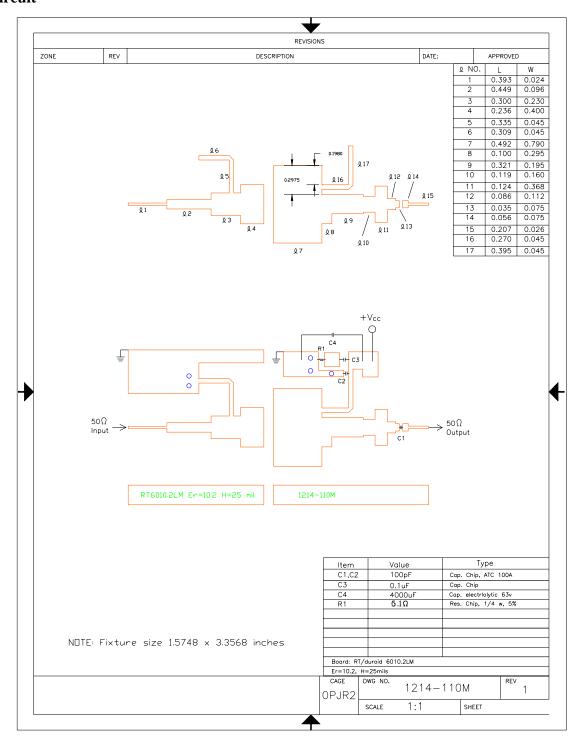
Note 2: Z_{Load} exclusive of bias circuit

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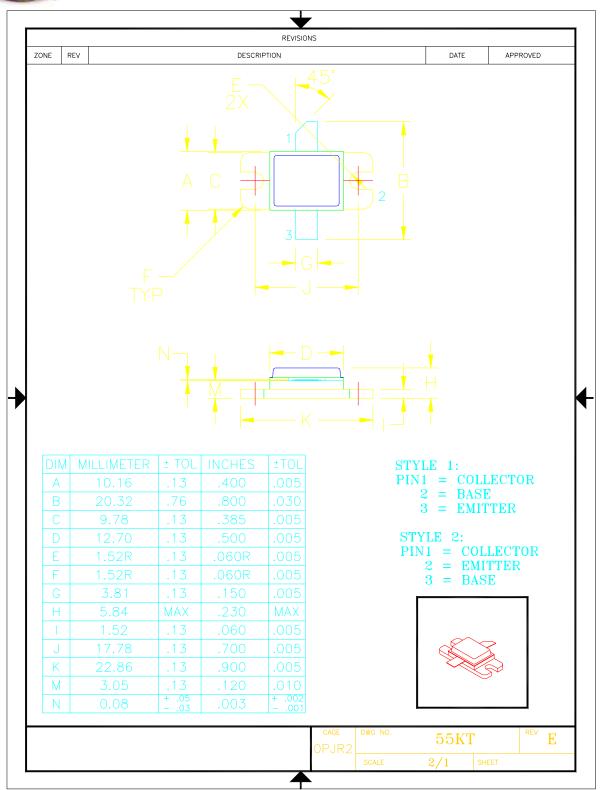
Test Circuit



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